

CMPT5401
SURFACE MOUNT
PNP SILICON TRANSISTOR



SOT-23 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT5401 type is a PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high voltage amplifier applications.

MARKING CODE: C2L

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	160	V
Collector-Emitter Voltage	V_{CEO}	150	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	600	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=120\text{V}$		50	nA
I_{CBO}	$V_{CB}=120\text{V}, T_A=100^\circ\text{C}$		50	μA
I_{EBO}	$V_{EB}=3.0\text{V}$		50	nA
BV_{CBO}	$I_C=100\mu\text{A}$	160		V
BV_{CEO}	$I_C=1.0\text{mA}$	150		V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.2	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.5	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		1.0	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		1.0	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	50		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	60	240	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=50\text{mA}$	50		
f_T	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100	300	MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		6.0	pF
h_{fe}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	40	200	
N_F	$V_{CE}=5.0\text{V}, I_C=250\mu\text{A}, R_S=1.0\text{k}\Omega,$ $f=10\text{Hz to } 15.7\text{kHz}$		8.0	dB

R6 (1-February 2010)

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SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Base
- 2) Emitter
- 3) Collector

MARKING CODE: C2L

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R6 (1-February 2010)

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